

# Keiji Ueno

## List of Publications by Year in descending order

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149  
papers

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101543

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151  
docs citations

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times ranked

6855  
citing authors

#	ARTICLE	IF	CITATIONS
1	Mist chemical vapor deposition of crystalline MoS <sub>2</sub> atomic layer films using sequential mist supply mode and its application in field-effect transistors. <i>Nanotechnology</i> , 2022, 33, 045601.	2.6	6
2	Quantitative Determination of Contradictory Bandgap Values of Bulk PdSe <sub>2</sub> from Electrical Transport Properties. <i>Advanced Functional Materials</i> , 2022, 32, 2108061.	14.9	11
3	Photoinduced Tellurium Segregation in MoTe <sub>2</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , 2022, 16, .	2.4	10
4	Mist chemical vapor deposition of Al <sub>1-x</sub> Ti <sub>x</sub> O <sub>y</sub> thin films and their application to a high dielectric material. <i>Journal of Applied Physics</i> , 2022, 131, 105301.	2.5	2
5	Ultrafast Operation of 2D Heterostructured Nonvolatile Memory Devices Provided by the Strong Short-Time Dielectric Breakdown Strength of h-BN. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 25659-25669.	8.0	4
6	Reversible Charge Polarity Control for Multioperation Mode Transistors Based on van der Waals Heterostructures. <i>Advanced Science</i> , 2022, 9, .	11.2	6
7	Enhanced Exciton Exciton Collisions in an Ultraflat Monolayer MoSe <sub>2</sub> Prepared through Deterministic Flattening. <i>ACS Nano</i> , 2021, 15, 1370-1377.	14.6	9
8	AlO <sub>x</sub> Thin Films Synthesized by Mist Chemical Vapor Deposition, Monitored by a Fast-Scanning Mobility Particle Analyzer, and Applied as a Gate Insulating Layer in the Field-Effect Transistors. <i>ACS Applied Electronic Materials</i> , 2021, 3, 658-667.	4.3	4
9	State-of-the-Art of Solution-Processed Crystalline Silicon/Organic Heterojunction Solar Cells: Challenges and Future. <i>Challenges and Advances in Computational Chemistry and Physics</i> , 2021, , 33-56.	0.6	1
10	Material and Device Structure Designs for 2D Memory Devices Based on the Floating Gate Voltage Trajectory. <i>ACS Nano</i> , 2021, 15, 6658-6668.	14.6	16
11	Intrinsic Electronic Transport Properties and Carrier Densities in PtS <sub>2</sub> and SnSe <sub>2</sub> : Exploration of n-Si Source for 2D Tunnel FETs. <i>Advanced Electronic Materials</i> , 2021, 7, 2100292.	5.1	8
12	Twist Angle-Dependent Interlayer Exciton Lifetimes in van der Waals Heterostructures. <i>Physical Review Letters</i> , 2021, 126, 047401.	7.8	88
13	Low-temperature growth of crystalline tungsten disulfide thin films by using organic liquid precursors. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SCCC04.	1.5	4
14	Improved efficiency of methylammonium-free perovskite thin film solar cells by fluorinated ammonium iodide treatment. <i>Organic Electronics</i> , 2020, 78, 105596.	2.6	15
15	Self-assembled Fluorinated Polymer Passivation Layer for Efficient Perovskite Thin-film Solar Cells. <i>Chemistry Letters</i> , 2020, 49, 87-90.	1.3	6
16	All 2D Heterostructure Tunnel Field-Effect Transistors: Impact of Band Alignment and Heterointerface Quality. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 51598-51606.	8.0	35
17	Effect of thermally annealed atomic-layer-deposited AlO <sub>x</sub> /chemical tunnel oxide stack layer at the PEDOT:PSS/n-type Si interface to improve its junction quality. <i>Journal of Applied Physics</i> , 2020, 128, 045305.	2.5	3
18	Facile and Reversible Carrier-Type Manipulation of Layered MoTe <sub>2</sub> Toward Long-Term Stable Electronics. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 42918-42924.	8.0	4

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19	Exciton diffusion in hBN-encapsulated monolayer MoSe <sub>2</sub> . <i>Physical Review B</i> , 2020, 102, .	3.2	12
20	Understanding the Memory Window Overestimation of 2D Materials Based Floating Gate Type Memory Devices by Measuring Floating Gate Voltage. <i>Small</i> , 2020, 16, e2004907.	10.0	11
21	Synthesis of AlO <sub>x</sub> thin films by atmospheric-pressure mist chemical vapor deposition for surface passivation and electrical insulator layers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	2.1	4
22	Ultrafast dynamics of the low frequency shear phonon in 1Tâ€²-MoTe <sub>2</sub> . <i>Applied Physics Letters</i> , 2020, 116, .	3.3	21
23	Flat bands in twisted bilayer transition metal dichalcogenides. <i>Nature Physics</i> , 2020, 16, 1093-1096.	16.7	197
24	Investigation of laser-induced-metal phase of MoTe <sub>2</sub> and its contact property via scanning gate microscopy. <i>Nanotechnology</i> , 2020, 31, 205205.	2.6	11
25	Role of the solvent in large crystal grain growth of inorganic-organic halide FA <sub>0.8</sub> Cs <sub>0.2</sub> Pb <sub>1-x</sub> Br <sub>3</sub> perovskite thin films monitored by ellipsometry. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019, 37, .		2
26	Barrier Formation at the Contacts of Vanadium Dioxide and Transition-Metal Dichalcogenides. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 36871-36879.	8.0	9
27	Exciton Diffusion in hBN-encapsulated Monolayer MoSe <sub>2</sub> . , 2019, , .		0
28	Highly crystalline large-grained perovskite films using two additives without an antisolvent for high-efficiency solar cells. <i>Thin Solid Films</i> , 2019, 679, 27-34.	1.8	7
29	Oxygen-Sensitive Layered MoTe <sub>2</sub> Channels for Environmental Detection. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 47047-47053.	8.0	13
30	Selective oxidation of the surface layer of bilayer WSe <sub>2</sub> by laser heating. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 120903.	1.5	6
31	Site-dependence of relationships between photoluminescence and applied electric field in monolayer and bilayer molybdenum disulfide. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 015001.	1.5	1
32	Gate-Tunable Thermal Metal-Insulator Transition in VO <sub>2</sub> Monolithically Integrated into a WSe <sub>2</sub> Field-Effect Transistor. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 3224-3230.	8.0	29
33	Reversible and Precisely Controllable p/n-Type Doping of MoTe <sub>2</sub> Transistors through Electrothermal Doping. <i>Advanced Materials</i> , 2018, 30, e1706995.	21.0	68
34	Optical Anisotropy and Compositional Ratio of Conductive Polymer PEDOT:PSS and Their Effect on Photovoltaic Performance of Crystalline Silicon/Organic Heterojunction Solar Cells. , 2018, , 137-159.		4
35	Pronounced photogating effect in atomically thin WSe <sub>2</sub> with a self-limiting surface oxide layer. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	38
36	Ultrathin Bismuth Film on 1T-TaS <sub>2</sub> : Structural Transition and Charge-Density-Wave Proximity Effect. <i>Nano Letters</i> , 2018, 18, 3235-3240.	9.1	28

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37	Self-passivated ultra-thin SnS layers via mechanical exfoliation and post-oxidation. <i>Nanoscale</i> , 2018, 10, 22474-22483.	5.6	42
38	Fabrication of $[\text{CH}(\text{NH}_2)_2]_{0.8}\text{Cs}_{0.2}\text{PbI}_3$ Perovskite Thin Films for n-i-p Planar-structure Solar Cells by a One-step Method Using 1-Cyclohexyl-2-pyrrolidone as an Additive. <i>Chemistry Letters</i> , 2018, 47, 905-908.	1.3	7
39	2D Tunnel Field Effect Transistors (FETs) with a Stable Charge Transfer Type $\text{p}^+\text{WSe}_2$ Source. <i>Advanced Electronic Materials</i> , 2018, 4, 1800207.	5.1	41
40	Fabrication and Surface Engineering of Two-Dimensional SnS Toward Piezoelectric Nanogenerator Application. <i>MRS Advances</i> , 2018, 3, 2809-2814.	0.9	19
41	Anisotropic band splitting in monolayer NbSe <sub>2</sub> : implications for superconductivity and charge density wave. <i>Npj 2D Materials and Applications</i> , 2018, 2, .	7.9	43
42	Fabrication of $\{\text{CH}(\text{NH}_2)_2\}_{1-x}\text{Cs}_x\text{PbI}_3$ Perovskite Thin Films by Two-step Method and Its Application to Thin Film Solar Cells. <i>Chemistry Letters</i> , 2017, 46, 612-615.	1.3	5
43	Sensitive Phonon-Based Probe for Structure Identification of 1T MoTe <sub>2</sub> . <i>Journal of the American Chemical Society</i> , 2017, 139, 8396-8399.	13.7	46
44	Barium hydroxide hole blocking layer for front- and back-organic/crystalline Si heterojunction solar cells. <i>Journal of Applied Physics</i> , 2017, 122, .	2.5	26
45	Exfoliation and van der Waals heterostructure assembly of intercalated ferromagnet $\text{Cr}_{1/3}\text{TaS}_2$ . <i>2D Materials</i> , 2017, 4, 041007.	4.4	41
46	Effect of substrate bias on mist deposition of conjugated polymer on textured crystalline Si for efficient Si/organic heterojunction solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1922-1925.	1.8	8
47	Monolayer 1T-NbSe <sub>2</sub> as a Mott insulator. <i>NPG Asia Materials</i> , 2016, 8, e321-e321.	7.9	109
48	Correlation between the fine structure of spin-coated PEDOT:PSS and the photovoltaic performance of organic/crystalline-silicon heterojunction solar cells. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	46
49	Carrier Polarity Control in $\pm$ -MoTe <sub>2</sub> Schottky Junctions Based on Weak Fermi-Level Pinning. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 14732-14739.	8.0	72
50	Investigating the chemical mist deposition technique for poly(3,4-ethylenedioxythiophene):poly(styrene sulfonate) on textured crystalline-silicon for organic/crystalline-silicon heterojunction solar cells. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 031601.	1.5	16
51	Synthesis of High-Quality Large-Area Homogenous 1T MoTe <sub>2</sub> from Chemical Vapor Deposition. <i>Advanced Materials</i> , 2016, 28, 9526-9531.	21.0	125
52	Nafion-Modified PEDOT:PSS as a Transparent Hole-Transporting Layer for High-Performance Crystalline-Si/Organic Heterojunction Solar Cells with Improved Light Soaking Stability. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 31926-31934.	8.0	63
53	Role of Isopropyl Alcohol Solvent in the Synthesis of Organic-Inorganic Halide $\text{CH}(\text{NH}_2)_2\text{PbI}_2\text{Br}_3$ Perovskite Thin Films by a Two-Step Method. <i>Journal of Physical Chemistry C</i> , 2016, 120, 25371-25377.	3.1	12
54	Solution-processed crystalline silicon double-heterojunction solar cells. <i>Applied Physics Express</i> , 2016, 9, 022301.	2.4	15

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55	Self-Limiting Oxides on WSe <sub>2</sub> as Controlled Surface Acceptors and Low-Resistance Hole Contacts. Nano Letters, 2016, 16, 2720-2727.	9.1	131
56	Introduction to the Growth of Bulk Single Crystals of Two-Dimensional Transition-Metal Dichalcogenides. Journal of the Physical Society of Japan, 2015, 84, 121015.	1.6	36
57	Highly Efficient Solution-Processed Poly(3,4-ethylenedioxythiophene):Poly(styrenesulfonate)/Crystalline Silicon Heterojunction Solar Cells with Improved Light-Induced Stability. Advanced Energy Materials, 2015, 5, 1500744.	19.5	85
58	Origin of Noise in Layered MoTe <sub>2</sub> Transistors and its Possible Use for Environmental Sensors. Advanced Materials, 2015, 27, 6612-6619.	21.0	72
59	Solution-Processed Organic/Crystalline-Silicon Heterojunction Solar Cells with Improved Light-Induced Stability. , 2015, , .		0
60	Electrostatically Reversible Polarity of Ambipolar $\hat{1}\pm$ -MoTe <sub>2</sub> Transistors. ACS Nano, 2015, 9, 5976-5983.	14.6	113
61	van der Waals junctions of layered 2D materials for functional devices. , 2015, , .		0
62	Self-Limiting Layer-by-Layer Oxidation of Atomically Thin WSe <sub>2</sub> . Nano Letters, 2015, 15, 2067-2073.	9.1	204
63	Double resonance Raman modes in monolayer and few-layer $\text{MoTe}_2$ . Physical Review B, 2015, 91, .	3.2	99
64	Changes in structure and chemical composition of $\hat{1}\pm$ -MoTe <sub>2</sub> and $\hat{1}^2$ -MoTe <sub>2</sub> during heating in vacuum conditions. Applied Physics Express, 2015, 8, 095201.	2.4	36
65	Large-Area Synthesis of High-Quality Uniform Few-Layer MoTe <sub>2</sub> . Journal of the American Chemical Society, 2015, 137, 11892-11895.	13.7	302
66	Construction of van der Waals magnetic tunnel junction using ferromagnetic layered dichalcogenide. Applied Physics Letters, 2015, 107, .	3.3	47
67	Efficient organic/polycrystalline silicon hybrid solar cells. Nano Energy, 2015, 11, 260-266.	16.0	18
68	Fabrication of Organic/inorganic Hybrid CMOS Devices using Solution-processed Graphene Electrodes. IEEJ Transactions on Electronics, Information and Systems, 2015, 135, 156-159.	0.2	0
69	Improved performance of poly(3,4-ethylenedioxythiophene):poly(styrene sulfonate)/n-Si hybrid solar cell by incorporating silver nanoparticles. Japanese Journal of Applied Physics, 2014, 53, 110305.	1.5	7
70	Ambipolar MoTe <sub>2</sub> Transistors and Their Applications in Logic Circuits. Advanced Materials, 2014, 26, 3263-3269.	21.0	388
71	Real-time measurement of optical anisotropy during film growth using a chemical mist deposition of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate). Journal of Applied Physics, 2014, 115, 123514.	2.5	9
72	Self-assembled silver nanowires as top electrode for poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/n-silicon solar cell. Thin Solid Films, 2014, 558, 306-310.	1.8	16

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73	Improved photovoltaic response by incorporating green tea modified multiwalled carbon nanotubes in organic-inorganic hybrid solar cell. Canadian Journal of Physics, 2014, 92, 849-852.	1.1	2
74	Self assembled silver nanowire mesh as top electrode for organic-inorganic hybrid solar cell. Canadian Journal of Physics, 2014, 92, 867-870.	1.1	7
75	Strong Enhancement of Raman Scattering from a Bulk-Inactive Vibrational Mode in Few-Layer MoTe <sub>2</sub> . ACS Nano, 2014, 8, 3895-3903.	14.6	275
76	High-performance top-gated monolayer SnS <sub>2</sub> field-effect transistors and their integrated logic circuits. Nanoscale, 2013, 5, 9666.	5.6	269
77	Green-tea modified multiwalled carbon nanotubes for efficient poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/n-silicon hybrid solar cell. Applied Physics Letters, 2013, 102, .	3.3	31
78	Efficient Organic Photovoltaic Cells Using MoO <sub>3</sub> Hole-Transporting Layers Prepared by Simple Spin-Cast of Its Dispersion Solution in Methanol. Japanese Journal of Applied Physics, 2013, 52, 020202.	1.5	4
79	Optical anisotropy in solvent-modified poly(3,4-ethylenedioxythiophene):poly(styrenesulfonic acid) and its effect on the photovoltaic performance of crystalline silicon/organic heterojunction solar cells. Applied Physics Letters, 2013, 102, .	3.3	43
80	Optical and carrier transport properties of graphene oxide based crystalline-Si/organic Schottky junction solar cells. Journal of Applied Physics, 2013, 114, .	2.5	4
81	Improved photovoltaic performance of crystalline-Si/organic Schottky junction solar cells using ferroelectric polymers. Applied Physics Letters, 2013, 103, .	3.3	24
82	Effects of molybdenum oxide molecular doping on the chemical structure of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) and on carrier collection efficiency of silicon/poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) heterojunction solar cells. Applied Physics Letters, 2013, 102, 183503.	3.3	22
83	Top-Contacted Organic Field-Effect Transistors with Graphene Electrodes Prepared by Laminate Transfer Method. Applied Physics Express, 2012, 5, 125104.	2.4	2
84	Electrospray Deposition of Poly(3-hexylthiophene) Films for Crystalline Silicon/Organic Hybrid Junction Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 061602.	1.5	5
85	Efficient Crystalline Si/Poly(ethylene dioxythiophene):Poly(styrene sulfonate):Graphene Oxide Composite Heterojunction Solar Cells. Applied Physics Express, 2012, 5, 032301.	2.4	28
86	Increased Organic Photovoltaic Cell Efficiency by Incorporating a Nonionic Fluorinated Surfactant Cathode Interlayer. Applied Physics Express, 2012, 5, 121601.	2.4	0
87	Ionic liquid-mediated epitaxy of high-quality C60 crystallites in a vacuum. CrystEngComm, 2012, 14, 4939.	2.6	24
88	Crystalline Silicon/Graphene Oxide Hybrid Junction Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NE22.	1.5	1
89	Electrospray-Deposited Poly(3,4-ethylenedioxythiophene):Poly(styrene sulfonate) for Poly(3-hexylthiophene):Phenyl-C <sub>61</sub> -Butyric Acid Methyl Ester Photovoltaic Cells. Japanese Journal of Applied Physics, 2012, 51, 10NE30.	1.5	6
90	Optical properties and carrier transport in c-Si/conductive PEDOT:PSS(GO) composite heterojunctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2075-2078.	0.8	13

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91	Efficient crystalline Si/organic hybrid heterojunction solar cells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 2101-2106.	0.8	8
92	Chemical mist deposition of graphene oxide and PEDOT:PSS films for crystalline Si/organic heterojunction solar cells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 2134-2137.	0.8	22
93	Real-time ellipsometric characterization of the initial growth stage of poly(3,4-ethylenedioxythiophene):poly(styrene sulfonate) films by electrospray deposition using N,N-dimethylformamide solvent solution. <i>Journal of Non-Crystalline Solids</i> , 2012, 358, 2520-2524.	3.1	8
94	Highly efficient crystalline silicon/Zonyl fluorosurfactant-treated organic heterojunction solar cells. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	102
95	Electrospray Deposition of Poly(3-hexylthiophene) Films for Crystalline Silicon/Organic Hybrid Junction Solar Cells. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 061602.	1.5	4
96	Crystalline Silicon/Graphene Oxide Hybrid Junction Solar Cells. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 10NE22.	1.5	5
97	Electrospray-Deposited Poly(3,4-ethylenedioxythiophene):Poly(styrene sulfonate) for Poly(3-hexylthiophene):Phenyl-C61-Butyric Acid Methyl Ester Photovoltaic Cells. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 10NE30.	1.5	3
98	Fabrication of Transparent and Flexible Organic Field-Effect Transistors with Solution-Processed Graphene Source/Drain and Gate Electrodes. <i>Applied Physics Express</i> , 2011, 4, 021603.	2.4	31
99	Bulk heterojunction organic photovoltaic cell fabricated by the electrospray deposition method using mixed organic solvent. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 229-231.	2.4	45
100	Depth profile characterization of spin-coated poly(3,4-ethylenedioxythiophene): poly(styrene sulfonic) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 307 Td (diox Applied Physics, 2011, 8, 3025-3028.	0.8	3
101	Atmospheric-pressure argon plasma etching of spin-coated 3,4-polyethylenedioxythiophene:polystyrenesulfonic acid (PEDOT:PSS) films for copper phthalocyanine (CuPc)/C60 heterojunction thin-film solar cells. <i>Thin Solid Films</i> , 2011, 519, 6834-6839.	1.8	12
102	Real-Time Ellipsometric Characterization of Initial Growth Stage of Poly(3,4-ethylene) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 307 Td (diox Applied Physics, 2011, 50, 081603.	1.5	7
103	Depth Profile Characterization of Spin-Coated Poly(3,4-ethylenedioxythiophene):Poly(styrene sulfonic) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 307 Td (diox Japanese Journal of Applied Physics, 2011, 50, 08JG02.	1.5	2
104	Efficient Organic Photovoltaic Cells Using Hole-Transporting MoO <sub>3</sub> Buffer Layers Converted from Solution-Processed MoS <sub>2</sub> Films. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 071604.	1.5	11
105	Surface Modification of Poly(3,4-ethylene dioxthiophene):Poly(styrene sulfonic acid) (PEDOT:PSS) Films by Atmospheric-Pressure Argon Plasma for Organic Thin-Film Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2011, 11, 8035-8039.	0.9	1
106	Real-Time Ellipsometric Characterization of Initial Growth Stage of Poly(3,4-ethylene) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 147 Td (diox Applied Physics, 2011, 50, 081603.	1.5	2
107	Real-Time Ellipsometric Characterization of the Initial Growth Stage of Poly(3,4-ethylene) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 147 Td (diox and Nanotechnology, 2011, 11, 8030-8034.	0.9	4
108	Origin of the ambipolar operation of a pentacene field-effect transistor fabricated on a poly(vinyl) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 147 Td (diox Applied Physics, 2011, 94, 083305.	3.3	29

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109	Nucleation on the substrate surfaces during liquid flux-mediated vacuum deposition of rubrene. <i>Journal of Crystal Growth</i> , 2008, 311, 163-166.	1.5	7
110	Nanotransfer of the Polythiophene Molecular Alignment onto the Step-Bunched Vicinal Si(111) Substrate. <i>Langmuir</i> , 2008, 24, 11605-11610.	3.5	11
111	Molecular Layer-by-Layer Growth of C <sub>60</sub> Thin Films by Continuous-Wave Infrared Laser Deposition. <i>Applied Physics Express</i> , 2008, 1, 015005.	2.4	39
112	Step-bunched Bi-terminated Si(111) surfaces as a nanoscale orientation template for quasisingle crystalline epitaxial growth of thin film phase pentacene. <i>Applied Physics Letters</i> , 2008, 93, 223303.	3.3	15
113	Effect of Organic Buffer Layer on Performance of Pentacene Field-Effect Transistor Fabricated on Natural Mica Gate Dielectric. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L913-L916.	1.5	9
114	Anisotropic Polymerization of a Long-Chain Diacetylene Derivative Langmuir-Blodgett Film on a Step-Bunched SiO <sub>2</sub> /Si Surface. <i>Langmuir</i> , 2006, 22, 5742-5747.	3.5	7
115	Structure of Organic Thin Films Grown on Surface-modified Tantalum Oxide. <i>Chemistry Letters</i> , 2006, 35, 746-747.	1.3	2
116	Fabrication of an Organic Field-effect Transistor on a Mica Gate Dielectric. <i>Chemistry Letters</i> , 2006, 35, 354-355.	1.3	10
117	In-situ measurement of molecular orientation of the pentacene ultrathin films grown on SiO <sub>2</sub> substrates. <i>Surface Science</i> , 2006, 600, 2518-2522.	1.9	27
118	Orientation Control of Standing Epitaxial Pentacene Monolayers Using Surface Steps and In-plane Band Dispersion Analysis by Angle Resolved Photoelectron Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2006, 965, 1.	0.1	3
119	Anodization of electrolytically polished Ta surfaces for enhancement of carrier injection into organic field-effect transistors. <i>Journal of Applied Physics</i> , 2005, 98, 114503.	2.5	26
120	Bulk-like pentacene epitaxial films on hydrogen-terminated Si(111). <i>Applied Physics Letters</i> , 2005, 87, 061917.	3.3	23
121	Scanning Tunneling Microscopy and Spectroscopy Study of LiBr/Si(001) Heterostructure. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L203-L205.	1.5	3
122	Methyl-terminated Si(111) surface as the ultra thin protection layer to fabricate position-controlled alkyl SAMs by using atomic force microscope anodic oxidation. <i>Surface Science</i> , 2004, 552, 46-52.	1.9	11
123	Visible light photoemission and negative electron affinity of single-crystalline CsCl thin films. <i>Surface Science</i> , 2003, 544, 220-226.	1.9	12
124	Accumulation and Depletion Layer Thicknesses in Organic Field Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L1408-L1410.	1.5	105
125	Nano-scale anodic oxidation on a Si() surface terminated by bilayer-GaSe. <i>Surface Science</i> , 2002, 514, 27-32.	1.9	9
126	Low-energy electron energy loss spectroscopy of monolayer and thick La@C[ <sub>82</sub> ] films grown on MoS <sub>2</sub> substrates. <i>AIP Conference Proceedings</i> , 2001, , .	0.4	0



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127	Electron-energy-loss spectroscopy of KxC60 and K-halides: comparison in the K3p excitation region. Applied Surface Science, 2001, 169-170, 184-187.	6.1	4
128	Fabrication of GaAs Quantum Dots on a Bilayer-GaSe Terminated Si(111) Substrate. Japanese Journal of Applied Physics, 2001, 40, 1888-1891.	1.5	13
129	Investigation of the growth mechanism of an InSe epitaxial layer on a MoS2 substrate. Journal of Crystal Growth, 2000, 219, 115-122.	1.5	28
130	Comparative Study on Surfaces of Single-Crystalline Substrates. From Dielectric Substance to Semiconductor and Metal. Layered Material Substrates.. Hyomen Kagaku, 2000, 21, 716-723.	0.0	0
131	Highly sensitive reflection high-energy electron diffraction measurement by use of micro-channel imaging plate. Review of Scientific Instruments, 2000, 71, 3478-3479.	1.3	15
132	A Novel Method to Fabricate a Molecular Quantum Structure: Selective Growth of C60on Layered Material Heterostructures. Japanese Journal of Applied Physics, 1999, 38, 511-514.	1.5	15
133	Fabrication of C60 nanostructures by selective growth on GaSe/MoS2 and InSe/MoS2 heterostructure substrates. Applied Surface Science, 1998, 130-132, 670-675.	6.1	7
134	Fabrication of Molecular Crystal Nanostructures by a Selective Growth Method.. Hyomen Kagaku, 1998, 19, 14-20.	0.0	2
135	Nanostructure Fabrication Using Selective Growth on Nanosize Patterns Drawn by a Scanning Probe Microscope. Japanese Journal of Applied Physics, 1997, 36, 4061-4064.	1.5	10
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